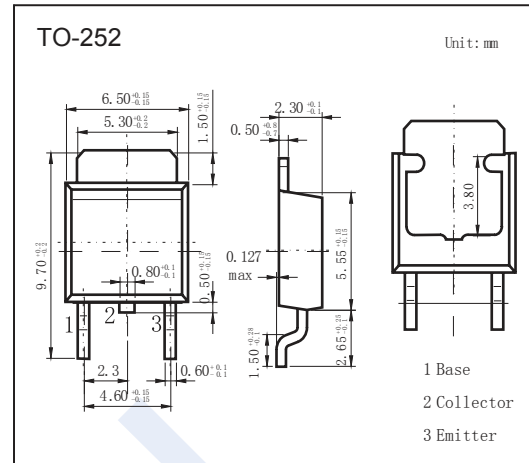


PNP Transistors

2SB768

■ Features

- High voltage: $V_{CEO} = -150V$
- Complimentary to 2SD1033.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-200	V
Collector - Emitter Voltage	V_{CEO}	-150	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-2	A
Collector Current - Pulse (Note.1)	I_{CP}	-3	
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10$ ms, Duty Cycle $\leq 50\%$.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-200			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1$ mA, $I_B = 0$	-150			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -150$ V, $I_E = 0$			-50	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4$ V, $I_C = 0$			-50	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA		-0.15	-1	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA			-1.2	
DC current gain (Note.1)	h_{FE}	$V_{CE} = -10$ V, $I_C = -400$ mA	40	80	200	
Transition frequency	f_T	$V_{CE} = -10$ V, $I_E = 0.4$ mA		10		MHz

Note.1: Pulse test : Pulse width $\leq 350 \mu s$, Duty Cycle $\leq 2\%$.

■ Classification of h_{FE}

Type	2SB768-M	2SB768-L	2SB768-K
Range	40-80	60-120	100-200

PNP Transistors

2SB768

■ Typical Characteristics

